

# Younghee Lee

## List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

23  
papers

1,038  
citations

19  
h-index

25  
g-index

25  
ext. papers

1,181  
ext. citations

8  
avg, IF

4.95  
L-index

#	Paper	IF	Citations
23	Thermal Atomic Layer Etching of Gallium Oxide Using Sequential Exposures of HF and Various Metal Precursors. <i>Chemistry of Materials</i> , <b>2020</b> , 32, 5937-5948	9.6	8
22	Thermal etching of AlF <sub>3</sub> and thermal atomic layer etching of Al <sub>2</sub> O <sub>3</sub> . <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , <b>2020</b> , 38, 022603	2.9	13
21	Thermal Atomic Layer Etching of Al <sub>2</sub> O <sub>3</sub> , HfO <sub>2</sub> , and ZrO <sub>2</sub> Using Sequential Hydrogen Fluoride and Dimethylaluminum Chloride Exposures. <i>Journal of Physical Chemistry C</i> , <b>2019</b> , 123, 18455-18466	3.8	25
20	In Situ Thermal Atomic Layer Etching for Sub-5 nm InGaAs Multigate MOSFETs. <i>Nano Letters</i> , <b>2019</b> , 19, 5159-5166	11.5	19
19	First Transistor Demonstration of Thermal Atomic Layer Etching: InGaAs FinFETs with sub-5 nm Fin-width Featuring in situ ALE-ALD <b>2018</b> ,		17
18	Thermal atomic layer etching of HfO <sub>2</sub> using HF for fluorination and TiCl <sub>4</sub> for ligand-exchange. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , <b>2018</b> , 36, 061504	2.9	29
17	Coating Solution for High-Voltage Cathode: AlF Atomic Layer Deposition for Freestanding LiCoO Electrodes with High Energy Density and Excellent Flexibility. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2017</b> , 9, 9614-9619	9.5	47
16	Thermal Atomic Layer Etching of Titanium Nitride Using Sequential, Self-Limiting Reactions: Oxidation to TiO <sub>2</sub> and Fluorination to Volatile TiF <sub>4</sub> . <i>Chemistry of Materials</i> , <b>2017</b> , 29, 8202-8210	9.6	52
15	Prospects for Thermal Atomic Layer Etching Using Sequential, Self-Limiting Fluorination and Ligand-Exchange Reactions. <i>ACS Nano</i> , <b>2016</b> , 10, 4889-94	16.7	90
14	Atomic Layer Deposition of Metal Fluorides Using HF/Pyridine as the Fluorine Precursor. <i>Chemistry of Materials</i> , <b>2016</b> , 28, 2022-2032	9.6	44
13	Cross-linked aluminum dioxybenzene coating for stabilization of silicon electrodes. <i>Nano Energy</i> , <b>2016</b> , 22, 202-210	17.1	24
12	Trimethylaluminum as the Metal Precursor for the Atomic Layer Etching of Al <sub>2</sub> O <sub>3</sub> Using Sequential, Self-Limiting Thermal Reactions. <i>Chemistry of Materials</i> , <b>2016</b> , 28, 2994-3003	9.6	65
11	Selectivity in Thermal Atomic Layer Etching Using Sequential, Self-Limiting Fluorination and Ligand-Exchange Reactions. <i>Chemistry of Materials</i> , <b>2016</b> , 28, 7657-7665	9.6	63
10	Mitigating irreversible capacity losses from carbon agents via surface modification. <i>Journal of Power Sources</i> , <b>2015</b> , 275, 605-611	8.9	12
9	Atomic Layer Deposition of AlF <sub>3</sub> Using Trimethylaluminum and Hydrogen Fluoride. <i>Journal of Physical Chemistry C</i> , <b>2015</b> , 119, 14185-14194	3.8	59
8	Surface-coating regulated lithiation kinetics and degradation in silicon nanowires for lithium ion battery. <i>ACS Nano</i> , <b>2015</b> , 9, 5559-66	16.7	99
7	Mechanism of Thermal Al <sub>2</sub> O <sub>3</sub> Atomic Layer Etching Using Sequential Reactions with Sn(acac) <sub>2</sub> and HF. <i>Chemistry of Materials</i> , <b>2015</b> , 27, 3648-3657	9.6	50

6	Atomic Layer Etching of HfO <sub>2</sub> Using Sequential, Self-Limiting Thermal Reactions with Sn(acac) <sub>2</sub> and HF. <i>ECS Journal of Solid State Science and Technology</i> , <b>2015</b> , 4, N5013-N5022	2	70
5	Atomic Layer Etching of AlF <sub>3</sub> Using Sequential, Self-Limiting Thermal Reactions with Sn(acac) <sub>2</sub> and Hydrogen Fluoride. <i>Journal of Physical Chemistry C</i> , <b>2015</b> , 119, 25385-25393	3.8	31
4	Atomic layer etching of Al <sub>2</sub> O <sub>3</sub> using sequential, self-limiting thermal reactions with Sn(acac) <sub>2</sub> and hydrogen fluoride. <i>ACS Nano</i> , <b>2015</b> , 9, 2061-70	16.7	104
3	Molecular layer deposition of aluminum alkoxide polymer films using trimethylaluminum and glycidol. <i>Langmuir</i> , <b>2011</b> , 27, 15155-64	4	39
2	Molecular Layer Deposition of Conductive Hybrid Organic-Inorganic Thin Films Using Diethylzinc and Hydroquinone. <i>ECS Transactions</i> , <b>2010</b> , 33, 191-195	1	30
1	Atomic Layer Deposition of LiOH and Li <sub>2</sub> CO <sub>3</sub> Using Lithium t-Butoxide as the Lithium Source. <i>ECS Transactions</i> , <b>2010</b> , 33, 223-229	1	47